



P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
- 12	0.031 at V _{GS} = - 4.5 V	- 7.6		
	0.041 at V _{GS} = - 2.5 V	- 6.6		
	0.054 at V _{GS} = - 1.8 V	- 5.8		

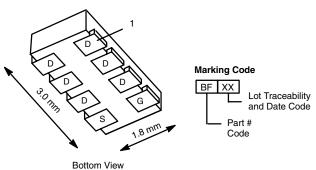
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs
- 1.8 V Rated
- · Compliant to RoHS Directive 2002/95/EC



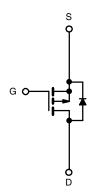


1206-8 ChipFET®



Ordering Information: Si5475DC-T1-E3 (Lead (Pb)-free)

Si5475DC-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unle	ss otherwise r	noted			
Parameter		Symbol	5 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 12		V	
Gate-Source Voltage		V _{GS}	± 8		V	
Continuous Dunin Comment /T 150 °C)	T _A = 25 °C	- I _D	- 7.6	- 5.5		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 85 °C		- 3.5	- 3.9		
Pulsed Drain Current		I _{DM}	± 20		Α	
Continuous Source Current ^a		I _S	- 2.1	- 1.1		
M	T _A = 25 °C	P _D	2.5	1.3	W	
Maximum Power Dissipation ^a	T _A = 85 °C		1.3	0.7		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		90	
Soldering Recommendations (Peak Temperature) ^{b, c}			260		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manifesture Investigat to Aughton 18	t ≤ 5 s	- R _{thJA}	40	50	°C/W
Maximum Junction-to-Ambient ^a	Steady State		80	95	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	15	20	

Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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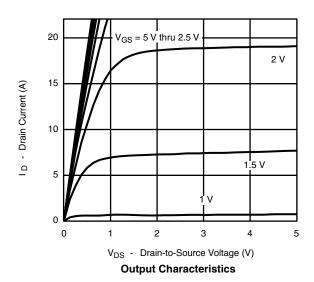
SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static								
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -1$ mA	- 0.45			٧		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 9.6 V, V _{GS} = 0 V			- 1			
		$V_{DS} = -9.6 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$			- 5	- μΑ		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 20			Α		
		V _{GS} = - 4.5 V, I _D = - 5.5 A		0.027	0.031			
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 4.8 A		0.035	0.041 Ω			
		V _{GS} = - 1.8 V, I _D = - 2 A		0.045	0.054			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 5.2 A		19		S		
Diode Forward Voltage ^a	V _{SD}	I _S = - 1.1 A, V _{GS} = 0 V		- 0.7	- 1.2	V		
Dynamic ^b								
Total Gate Charge	Q_g			19	29	nC		
Gate-Source Charge	Q _{gs}	$V_{DS} = -60 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -5.5 \text{ A}$		3.9				
Gate-Drain Charge	Q_{gd}			3.6				
Turn-On Delay Time	t _{d(on)}			15	25			
Rise Time	t _r	V_{DD} = - 6 V, R_L = 6 Ω		20	30			
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		122	180	ns		
Fall Time	t _f			80	120			
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.1 A, dI/dt = 100 A/μs		40	60			

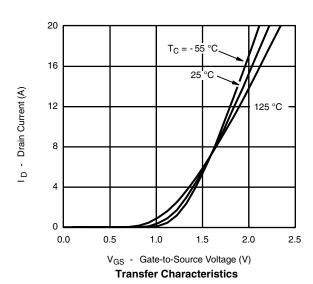
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



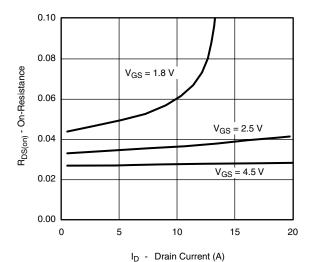




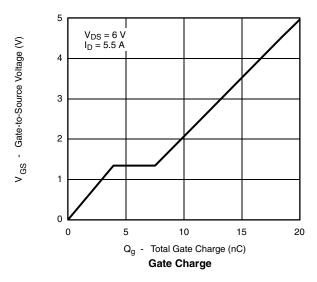


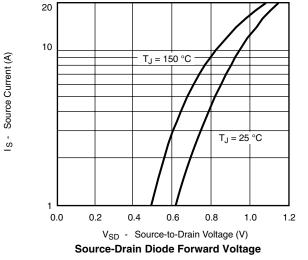


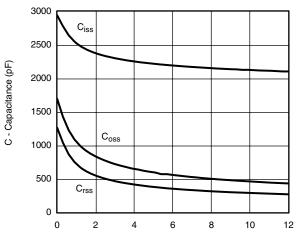
TYPICAL CHARACTERISTICS 25 °C unless noted



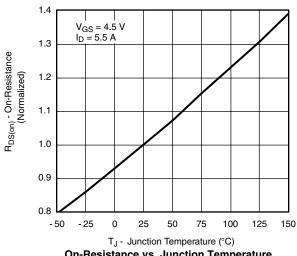
On-Resistance vs. Drain Current



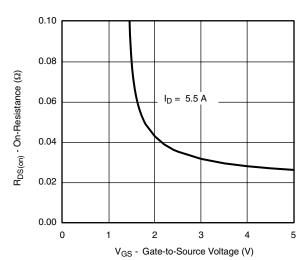




V_{DS} - Drain-to-Source Voltage (V) Capacitance



On-Resistance vs. Junction Temperature

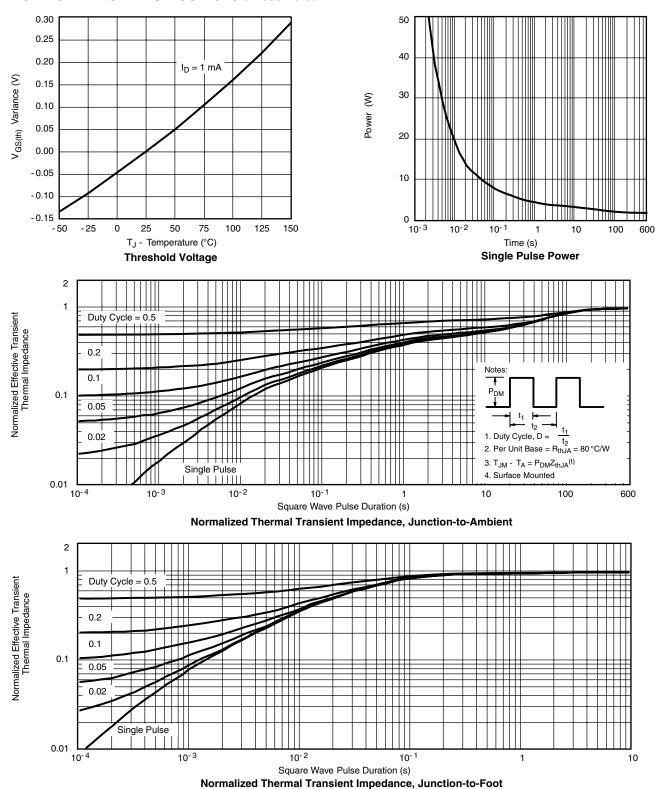


On-Resistance vs. Gate-to-Source Voltage

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TYPICAL CHARACTERISTICS 25 °C unless noted



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